

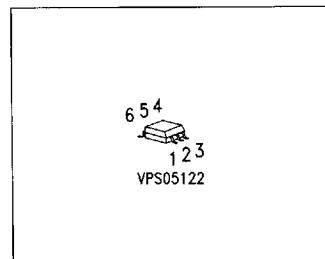
SIEMENS

High Voltage Level Shifter

BRM 10

Preliminary Data

- Power MOSFET Driver
- Floating supply
- Bootstrap operation
- CMOS compatible input
- Operating voltage up to 800 V
- Operating frequency up to 100 kHz

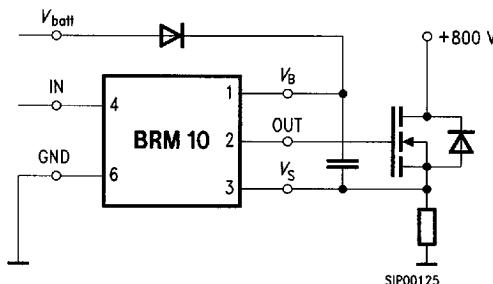


Type	Ordering Code	Information	Marking	Package
BRM 10	Q67000-S274	100 pcs per tube	BRM 10	P-DSO-6

Maximum Ratings

Parameter	Symbol	Values	Unit
Operating voltage	V_S	800	V
Voltage between V_B and V_S	V_{BS}	22	
Voltage between IN and Ground	V_{IN}	- 0.2 ... + 15	
Operating temperature range	T_j	- 40 ... + 150	°C
Storage temperature range	T_{stg}	- 55 ... + 150	
Max. power dissipation $T_A = 25^\circ\text{C}$	P_{tot}	0.6	W
Thermal resistance	R_{thJA}	220	K/W

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Pin Configuration**Pin Definitions and Functions**

Pin No.	Symbol	Function
1	V_B	Floating supply voltage
2	OUT	Output (Gate)
3	V_S	Output (Source)
4	IN	Input
5	-	Not connected
6	GND	Ground

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Electrical Characteristicsat $T_j = 25^\circ\text{C}$, $V_{\text{BS}} = 15\text{ V}$, unless otherwise specified.

Parameter and Conditions	Symbol	Values			Unit
		min.	typ.	max.	

Load Switching Capabilities and Characteristics

Output resistance	$V_{\text{IN}} = \text{low}$	R_{OUT}	—	40	—	Ω
Output voltage (OUT to V_S), no load		V_{OUT}	—	9.5	—	V
Short circuit output current	$V_{\text{IN}} = \text{high}$	I_{OUT}	—	150	—	mA
$V_{\text{IN}} = 10\text{ V}$, $C_L = 1\text{ nF}$, $V_S = 0\text{ V}$						μs
Delay turn-on time	to 10 % V_{OUT}	$t_{d(\text{on})}$	—	0.5	tbd	
Rise time	10 to 70 % V_{OUT}	t_r	—	0.3	tbd	
Delay turn-off time	to 90 % V_{OUT}	$t_{d(\text{off})}$	—	0.5	tbd	
Fall time	90 to 100 % V_{OUT}	t_f	—	0.25	tbd	
Critical rate of rise of V_S	$V_{\text{IN}} = 0\text{ V}$	— dV_S/dt	—	—	8	$\text{kV}/\mu\text{s}$
	$V_{\text{IN}} = 10\text{ V}$	— dV_S/dt	—	—	8	

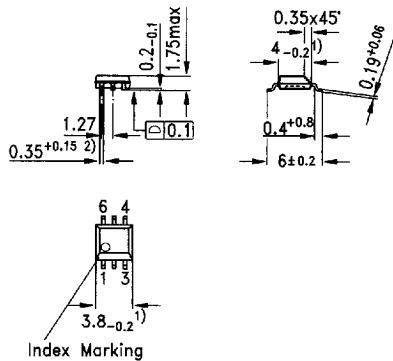
Input

Input turn-on threshold voltage		V_{IH}	tbd	2.6	—	V
Input turn-off threshold voltage		V_{IL}	—	2.2	tbd	
Off state input current	$V_{\text{IN}} = 0.4\text{ V}$	I_{IN}	—	20	—	μA
On state input current	$V_{\text{IN}} = 5\text{ V}$	$I_{IN(\text{on})}$	—	30	—	
	$V_{\text{IN}} = 10\text{ V}$		—	150	—	

Operating Parameters

Operating voltage	V_S	— 6	—	800	V
	V_{BS}	10	—	22	
Quiescent V_S supply current	$V_{\text{IN}} = 0\text{ V}$	I_{QS}	—	0.001	μA
$V_B = V_S = 800\text{ V}$	$V_{\text{IN}} = 10\text{ V}$		—	250	
Quiescent V_{BS} supply current	$V_{\text{IN}} = 0\text{ V}$	I_{QBS}	—	350	μA
$V_{\text{BS}} = 22\text{ V}$	$V_{\text{IN}} = 10\text{ V}$		—	260	
			—	1000	
			tbd		

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Package Outline**P-DSO-6**

1) Does not include plastic or metal protrusions of 0.15 max per side

Dimensions in mm

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Semiconductor Group

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